

Towards highly efficient and low cost quantum dot solar cells

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Research background

	Silicon solar cells	Perovskite thin film solar cells	Perovskite QD solar cells
Efficiency	26.3%	25.2%	18.1%
Cost	\$0.70 / Watt	\$0.35 / Watt	-
Stability	> 25 years	<2 years	-
Fabrication	High energy consumption	Low temperature Solution method	Room temperature Facile printing





Stability: 1. Shelling by ligand or other material 2. Enlarged surface energy

Low cost: Cheap raw material, solution

Facile fabrication: Printable



Outline:

- Improve performance: Composition and ligand management
- ✓ Advantage: QD vs Bulk
- ✓ Extended application: Semitransparent solar cell





Synthesis strategy



Direct synthesis of Cs_xFA_{1-x}Pbl₃ QDs is hard:

Crystallization is fast, within seconds.

Coordination force between A cations and PbI₆⁴⁻ cage is different: Cs⁺>OLA⁺>FA⁺

Cation exchange method:







Ligand assisted cation exchange





Optical and structure properties





- Tuneable light absorption and PL wavelength
- Black phase perovskite structure
- Uniform particle size ~14 nm



Distribution of A cation



${\rm In}\ {\rm Cs}_{\rm 0.5}{\rm FA}_{\rm 0.5}{\rm PbI}_{\rm 3}\ {\rm QDs}$

Small FAPbl₃ and CsPbl₃ domains randomly distributed within an single crystalline particle



Ligands and defects:



Ligand density in perovskite QD solutions

Purification times	CsPbl ₃	FAPbI ₃	
0	25-40	20-35	
1	2.5-5.5	9-15	
2	0.1-0.2	1-5	
	Cs _{1-x} FA _x PbI ₃		
0	2.5-10		
1	1.0-5.5		
2	0.1-0.5		

Atomic-resolution HAADF-STEM images of Cs_{0.5}FA_{0.5}Pbl₃ QDs obtained in OA-less condition (a, b) and Cs_{0.5}FA_{0.5}Pbl₃ QDs obtained in OA-rich condition (c, d). The circled areas indicate the defective sites.



Performance of Solar cell device

Device fabrication



- Separated process for crystallization and film formation
- Room temperature coating process

TEM cross-section image





NREL Best Research Cell Efficiencies





Defect reduction



The space charge–limited current (SCLC) measurements





Co-effect of FA alloying and rich ligands during synthesis



	CsPbI ₃	Cs _{0.5} FA _{0.5} P bl ₃ ligand rich	Cs _{0.5} FA _{0.5} P bl ₃ ligand poor
PCE (%)	9.6	16.1	10.1
V _{oc} (V)	1.16	1.13	1.08
l _{sc} (mA cm ⁻ ²)	15.4	18.4	14.6
FF (%)	53.9	77.9	64.1
Carrier lifetime (ns)	26	97	32
V _{tfl} (V)	0.092	0.207	0.275
Defect forming energy (ΔE_{I_i}) (eV)	0.40	0.65	-
Defect forming energy V _{Pb} (ΔE _{VPb}) (eV)	0.56	0.72	-



QDs vs bulk:



- Separated process for crystallization and film formation
- Room temperature coating process
- Ligand passivate defects and improve stability
- Impeded charge transport



- Large grain, high efficiency
- Substrate dependant
- Sensitive crystallinity control



QDs vs bulk: reduction of nonradiative charge recombination

Calculation from PLQY under $V_{\rm OC}$ condition





Device stability



✓ $Cs_{0.25}FA_{0.75}PbI_3$ -Bulk device. Quickly lost over 20% of initial efficiency

✓ $Cs_{0.25}FA_{0.75}PbI_3$ -QD devices. Retained **90%** of original PCEs.

✓ $Cs_{0.5}FA_{0.5}PbI_3$ -QD devices. Retained *94%* of original PCEs.



Suppressed phase segregation





Semitransparent





Thank you

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